

ABSTRACT

Embodiments of the present disclosure provide a semiconductor structure, including: a substrate, where the substrate is covered with a dielectric layer, and the dielectric layer includes a first region and a second region that surrounds the first region; a first conductive
5 pad disposed in the dielectric layer of the first region, where a top surface of the first conductive pad has a recessed or protruded part, and the dielectric layer covers the top surface of the first conductive pad; and a first bonding pad disposed in the dielectric layer of the second region, where the first bonding pad is disposed around the first conductive pad, the first bonding pad has a top surface exposed to the dielectric layer, and a bottom surface of the
10 first bonding pad is higher than the top surface of the first conductive pad. The semiconductor structure provided in the embodiments of the present disclosure has the second region disposed around a periphery of the first region, where the first bonding pad is disposed in the second region, and the first bonding pad can effectively prevent an impact of a protruded or recessed surface of the first region on a product yield.

15 [FIG. 1A]